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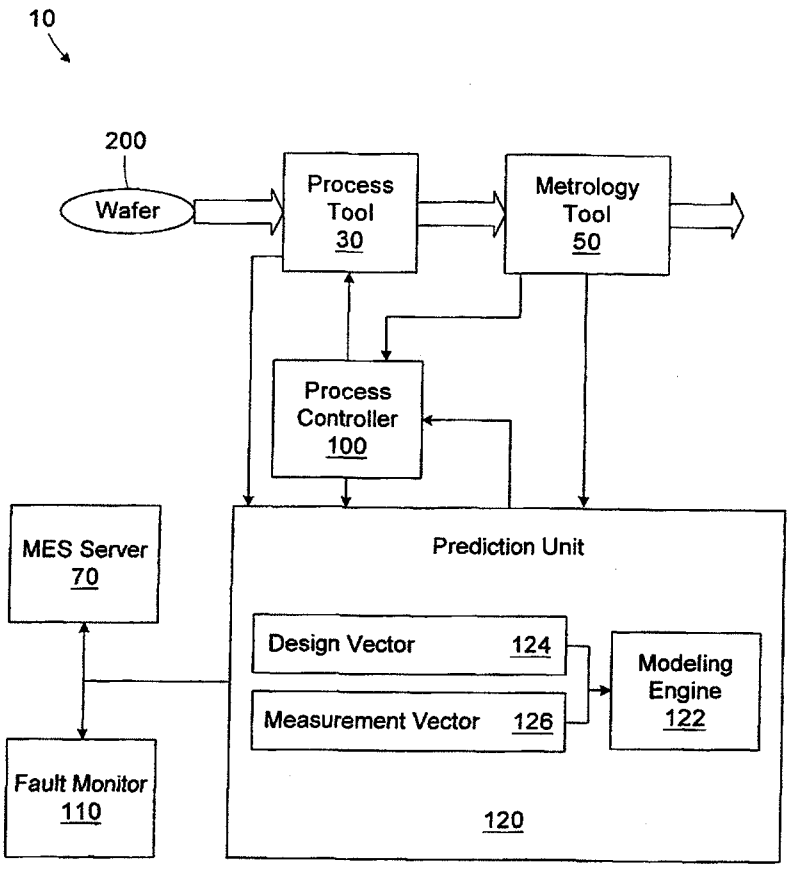
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(54) Title: METHOD AND APPARATUS FOR PREDICTING DEVICE ELECTRICAL PARAMETERS DURING FABRICATION



(57) Abstract: A method includes storing characteristics associated with the processing of a semiconductor device (200) collected during its fabrication. A vector (124) of initial characteristic values associated with the semiconductor device (200) is provided. The vector (124, 126) is updated with at least a subset of the collected characteristics. At least one electrical characteristic of the semiconductor device (200) is modeled based on the updated vector (124, 126). A system (10) includes a data store (90) and a prediction unit (130). The data store (90) is configured to store characteristics of a semiconductor device (200) collected during its fabrication. The prediction unit (130) is configured to provide a vector (124) of initial characteristics values associated with the semiconductor device (200), update the vector (124, 126) with at least a subset of the collected characteristics, and model at least one electrical characteristics of the semiconductor device (200) based on the updated vector (124, 126).

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